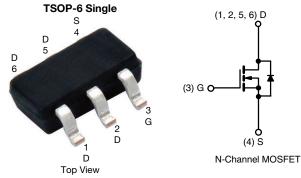


Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	60		
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.042		
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.063		
I _D (A)	7		
Configuration	Single		



FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>



COMPLIANT HALOGEN

ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free and Halogen-free	SQ3426EV-T1-GE3

ABSOLUTE MAXIMUM RATINGS	_C = 25 °C, unles	s otherwise noted)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	60	v
Gate-Source Voltage		V _{GS}	± 20	v
Continuous Drain Current	T _C = 25 °C	1-	7	
Continuous Drain Current	T _C = 125 °C	I _D	4	
Continuous Source Current (Diode Conduction)		I _S	6	А
Pulsed Drain Current ^a		I _{DM}	29	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	10	
Single Pulse Avalanche Energy		E _{AS}	5	mJ
Maximum Power Dissipation ^a	T _C = 25 °C	PD	5	w
	T _C = 125 °C	۳D	1.6	VV V
Operating Junction and Storage Temperature Ra	nge	T _J , T _{stg}	- 55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^b	R _{thJA}	110	°C/W
Junction-to-Foot (Drain)		R _{thJF}	30	0/10

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. When mounted on 1" square PCB (FR4 material).

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static							•	
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	60	-	-	v	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	: V _{GS} , I _D = 250 μA	1.5	2	2.5	v	
Gate-Source Leakage		$V_{DS} = 0 V, V_{GS} = \pm 12 V$		-	-	± 100	nA	
Gale-Source Leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20$ V	-	-	± 300	na	
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	150		
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 \text{ V}$	$V_{DS} \ge 5 V$	10	-	-	Α	
		$V_{GS} = 10 V$	I _D = 5 A	-	0.032	0.042	Ω	
Drain Course On State Desistance a		$V_{GS} = 10 V$	I _D = 5 A, T _J = 125 °C	-	0.056	-		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}$	I _D = 5 A, T _J = 175 °C	-	0.071	-		
		$V_{GS} = 4.5 V$	$I_D = 4 A$	-	0.035	0.063		
Forward Transconductance ^a	g _{fs}	V _{DS}	= 15 V, I _D = 4 A	-	21	-	S	
Dynamic ^b	<u>.</u>							
Input Capacitance	C _{iss}			-	560	720		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 30 V, f = 1 MHz	-	85	110	pF	
Reverse Transfer Capacitance	C _{rss}			-	55	70	1	
Total Gate Charge ^c	Qg			-	6.3	12		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 4.5 V	$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 4 \text{ A}$	-	2.1	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	4.1	-		
Gate Resistance	Rg		f = 1 MHz	1.9	3.8	5.7	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	9	14		
Rise Time ^c	tr	$V_{DD} = 30 \text{ V}, \text{ R}_{L} = 7.5 \Omega$		-	12	18		
Turn-Off Delay Time ^c	t _{d(off)}	I _D ≅ 4 A, ^v	$V_{ m GEN}$ = 10 V, R _g = 1 Ω	-	19	29	ns	
Fall Time ^c	t _f	1		-	7	11	1	
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	29	Α	
Forward Voltage	V _{SD}	$I_{\rm F} = 1.6 \text{A}, V_{\rm GS} = 0$		_	0.75	1.2	V	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

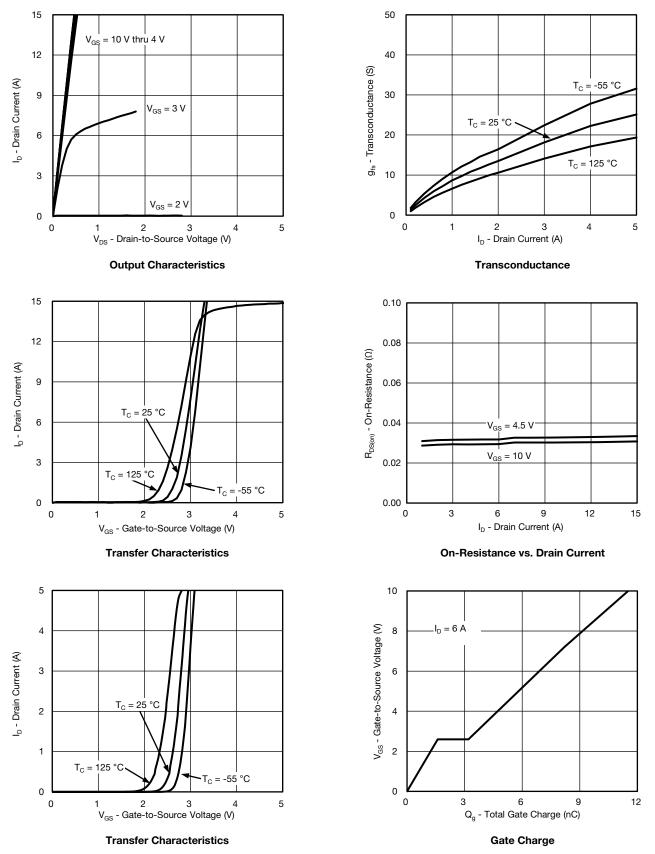
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2



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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



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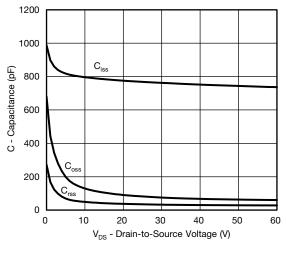
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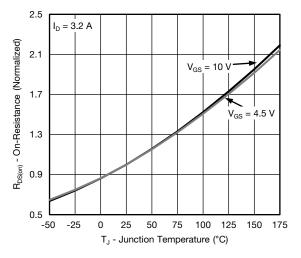


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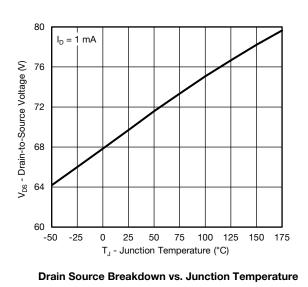
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)







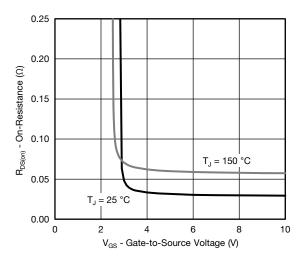
On-Resistance vs. Junction Temperature



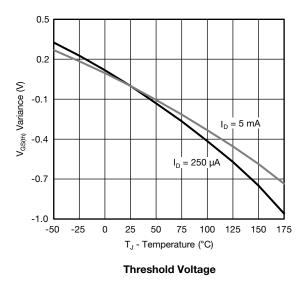
10 T_J = 150 °C I_s - Source Current (A) 1 0.1 T.I = 25 °C 0.01 0.001 0.2 0.0 0.4 0.6 0.8 1.0 1.2 V_{SD} - Source-to-Drain Voltage (V)

100

Source Drain Diode Forward Voltage



On-Resistance vs. Gate-Source Voltage



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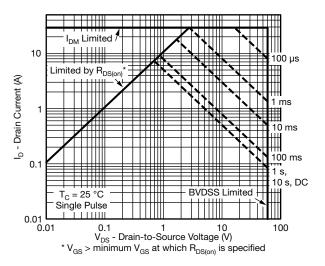
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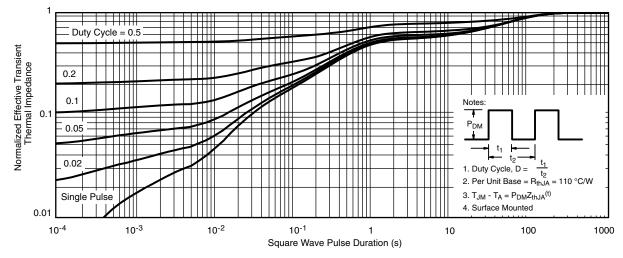


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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Safe Operating Area



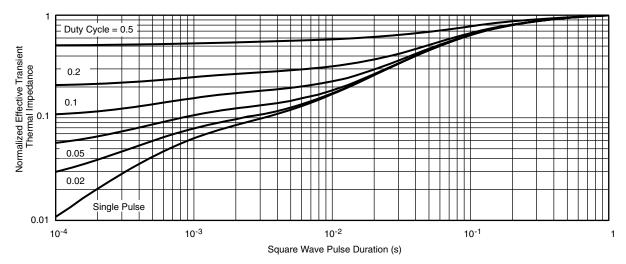
Normalized Thermal Transient Impedance, Junction-to-Ambient





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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized thermal Transient Impedance, Junction-to-Foot

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction to Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65107.



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TSOP-6

Ordering codes for the SQ rugged series power MOSFETs in the TSOP-6 package:

DATASHEET PART NUMBER	OLD ORDERING CODE ^a	NEW ORDERING CODE	
SQ3410EV	SQ3410EV-T1-GE3	SQ3410EV-T1_GE3	
SQ3418EV	-	SQ3418EV-T1_GE3	
SQ3419AEEV	-	SQ3419AEEV-T1_GE3	
SQ3419EV	-	SQ3419EV-T1_GE3	
SQ3426AEEV	-	SQ3426AEEV-T1_GE3	
SQ3426EV	-	SQ3426EV-T1_GE3	
SQ3427AEEV	-	SQ3427AEEV-T1_GE3	
SQ3427EV	-	SQ3427EV-T1_GE3	
SQ3456BEV	SQ3456BEV-T1-GE3	SQ3456BEV-T1_GE3	
SQ3457EV	SQ3457EV-T1-GE3	SQ3457EV-T1_GE3	
SQ3460EV	SQ3460EV-T1-GE3	SQ3460EV-T1_GE3	
SQ3461EV	- SQ3461EV-T1_0		
SQ3469EV	SQ3469EV-T1-GE3	SQ3469EV-T1_GE3	
SQ3481EV	SQ3481EV-T1-GE3	SQ3481EV-T1_GE3	
SQ3985EV	-	SQ3985EV-T1_GE3	

Note

a. Old ordering code is obsolete and no longer valid for new orders



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